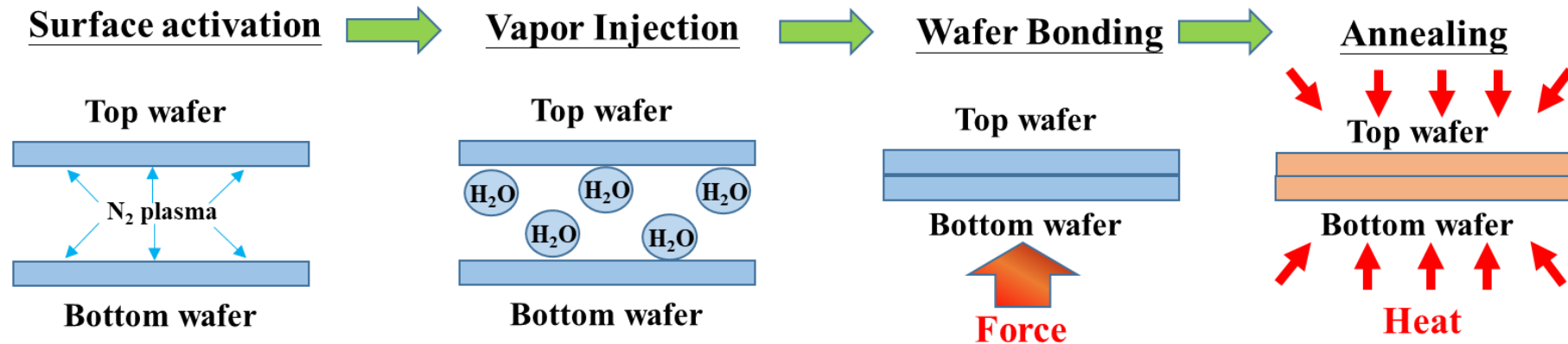


Standard Procedures of Bonder



- **Wafer Bonding :** This process offers standard oxide-to-oxide and wafer-to-wafer bonding techniques. The wafer surface is activated with nitrogen plasma, followed by the introduction of water vapor to prepare for subsequent hydrogen bonding. Finally, an external force is applied to bond the two wafers together.
- **Post Annealing :** After the wafer is bonded, the temperature is increased to 300°C and maintained for 2 hours. This process further removes moisture and enhances bonding strength. The heating rate is set at $1^{\circ}\text{C}/\text{min}$.